Exam Seat No: _____ **C.U.SHAH UNIVERSITY Summer Examination-2018**

Subject Name: Advances in Solid state Electronic Devices

Subject Code: 5SC	04ASS1	Branch: M.Sc. (Physics)		
Semester: 4	Date: 08/05/2018	Time: 10:30 To 01:30	Marks: 70	

Instructions:

- (1) Use of Programmable calculator and any other electronic instrument is prohibited.
- (2) Instructions written on main answer book are strictly to be obeyed.
- (3) Draw neat diagrams and figures (if necessary) at right places.
- (4) Assume suitable data if needed.

SECTION – I

Q-1			Attempt the Following questions.	(07)				
		a.	Give full form of HBT's.	(01)				
		b.	Give the types of regions in I-V characteristics of JFET distributed.	(01)				
		c.	Define pinch-off voltage V_p and gives its formula for JFET.	(02)				
		d.	What is MODFET?	(01)				
		e.	Draw only schematic of MODFET device structure.	(02)				
Q-2			Attempt all questions	(14)				
	A		Explain in details Saturation regime in current-Voltage characteristic of JFET.	(09)				
	B		Explain in details GaAs/AlGaAs HBT's in details.	(05)				
	OR							
Q-2			Attempt all questions	(14)				
	A		Explain in details InGaAs/InAlAs and InGaAs/ InP HBT's in details.	(08)				
	B		Write a short note on MODFET.	(06)				
Q-3			Attempt all questions	(14)				
	A		Explain in details Ohmic regime in current-Voltage characteristic of JFET.	(09)				
	B		Explain Si- Based HBT's in details.	(05)				
			OR					
Q-3			Attempt all questions	(14)				
	Α		Explain in details I-V characteristics of MODFET with different types of regions.	(08)				
	B		Why need for band tailoring and HBT's.	(06)				
	SECTION – II							
Q-4			Attempt the Following questions.	(07)				
		a.	Which types of material used for light emitting devices.	(01)				
		b.	Give names of advanced LED structures.	(01)				
		c.	Define MOSFET and gives its types.	(02)				
		d.	Write basic operating principle of Photoconductors and give its types.	(02)				



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		e.	What is impact ionization?	(01)				
Q-5			Attempt all questions	(14)				
	Α		Write a short note on Hetrojunction LEDs.	(06)				
	В		Explain in details depletion type MOSFET with proper circuit diagram.	(08)				
			OR					
Q-5			Attempt all questions	(14)				
	Α		Explain in details MOS Capacitor and its accumulation, Depletion and Inversion regions.	(08)				
	B		Explain in details Surface emitting LEDs.	(06)				
Q-6			Attempt all questions	(14)				
	Α		Explain in details current-Voltage characteristics of MOSFET and give its parameters.	(08)				
	В		Explain in details edge emitting LEDs.	(06)				
	OR							
Q-6			Attempt all Questions	(14)				
C	Α		Explain in details Complementary MOSFET.	(05)				
	B		Explain in details operating principle and characteristics of LASER Diode.	(06)				
	С		Explain in details Light- current characteristics of LED.	(03)				

